

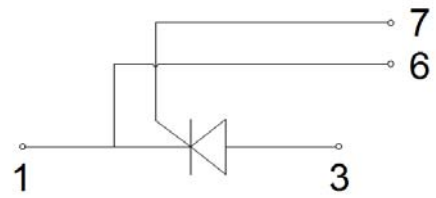
Thyristor Modules

V_{RRM} / V_{DRM} 800 to 1800V
I_{TAV} 200A

Applications

- Power Converters
- Lighting Control
- DC Motor Control and Drives
- Heat and temperature control

Circuit



Features

- International standard package
- High Surge Capability
- Glass passivated chip
- Simple Mounting
- Heat transfer through aluminum oxide DBC ceramic isolated metal baseplate

Module Type

TYPE	V_{RRM}	V_{RSM}
MT200U08T2	800V	900V
MT200U12T2	1200V	1300V
MT200U16T2	1600V	1700V
MT200U18T2	1800V	1900V

Maximum Ratings

Symbol	Conditions	Values	Units
I_{TAV}	Sine 180°;Tc=85℃	200	A
I_{TSM}	T_{VJ}=45℃ t=10ms, sine T_{VJ}=125℃ t=10ms, sine	5500 5000	A
i^2t	T_{VJ}=45℃ t=10ms, sine T_{VJ}=125℃ t=10ms, sine	151000 125000	A2s
Visol	a.c.50HZ;r.m.s.;1min	3000	V
Tvj		-40 to 130	℃
Tstg		-40 to 125	℃
Mt	To terminals(M6)	3±15%	Nm
Ms	To heat sink(M6)	5±15%	Nm
di/dt	T_{VJ}= T_{VJM} , 2/3V_{DRM} ,I_G =500mA Tr<0.5us,tp>6us	200	A/us
dv/dt	T_J= T_{VJM} ,2/3V_{DRM}, linear voltage rise	1000	V/us
a	Maximum allowable acceleration	50	m/s^2
Weight	Module(Approximately)	165	g

Thermal Characteristics

Symbol	Conditions	Values	Units

Electrical Characteristics

Symbol	Conditions	Values			Units
		Min.	Typ.	Max.	
V_{TM}	T=25℃ I_{TM} =500A			1.68	V
I_{RRM}/I_{DRM}	T_{VJ} =T_{VJM} ,V_R=V_{RRM} ,V_D=V_{DRM}			50	mA
V_{TO}	For power-loss calculations only (T_{VJ} =125℃)			0.85	V
r_T	T_{VJ} =T_{VJM}			1.5	mΩ
V_{GT}	T_{VJ} =25℃ , V_D =6V			3	V
I_{GT}	T_{VJ} =25℃ , V_D =6V			200	mA
V_{GD}	T_{VJ} =125℃ , V_D =2/3V_{DRM}			0.25	V
I_{GD}	T_{VJ} =125℃ , V_D =2/3V_{DRM}			10	mA
I_L	T_{VJ} =25℃ , R_G = 33 Ω		300	1000	mA
I_H	T_{VJ} =25℃ , V_D =6V		150	400	mA
tgd	T_{VJ} =25℃, I_G=1A, di_G/dt=1A/us		1		us
tq	T_{VJ} =T_{VJM}		100		us

Performance Curves

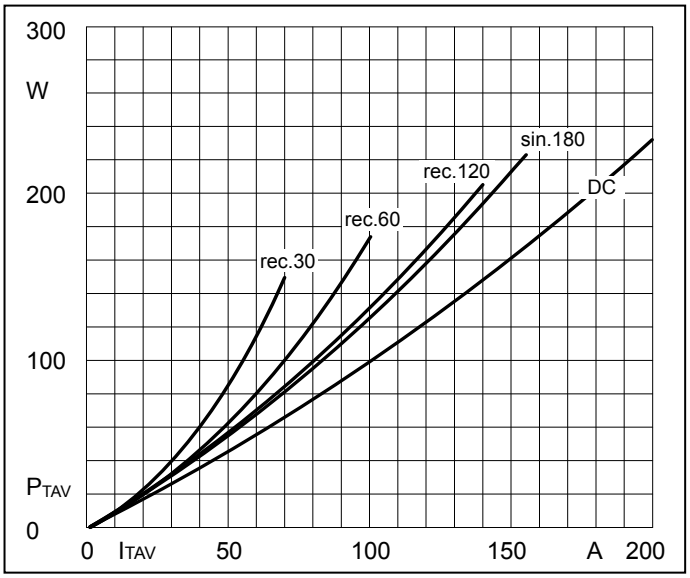


Fig1. Power dissipation

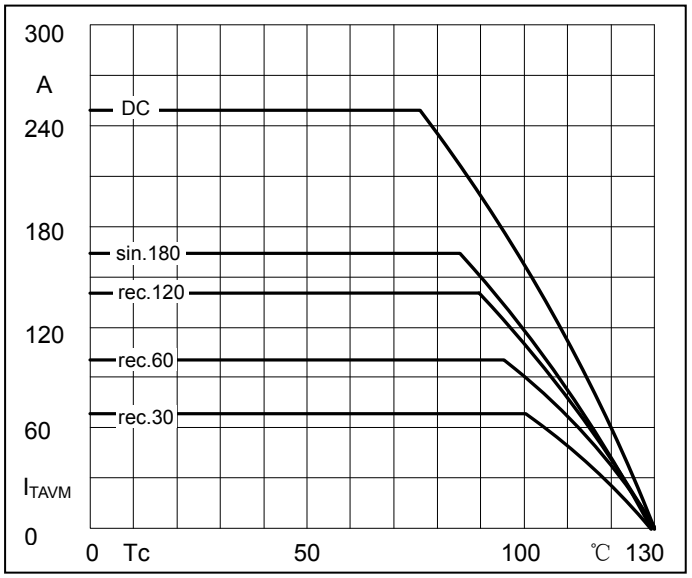


Fig2.Forward Current Derating Curve

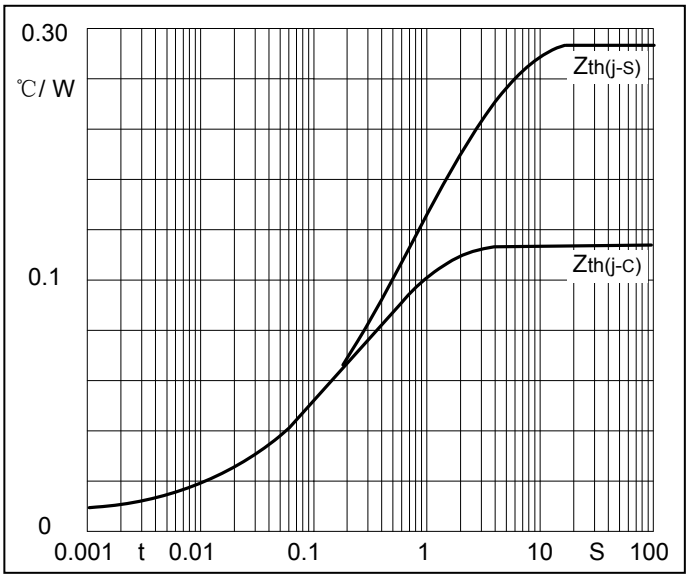


Fig3. Transient thermal impedance

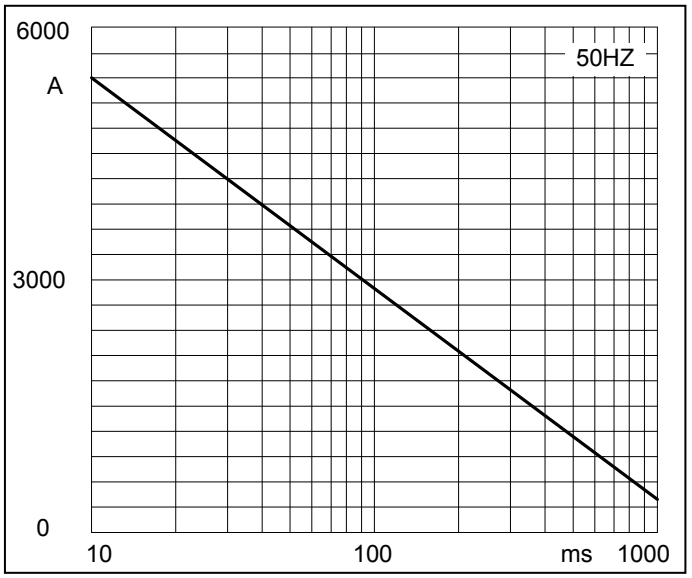
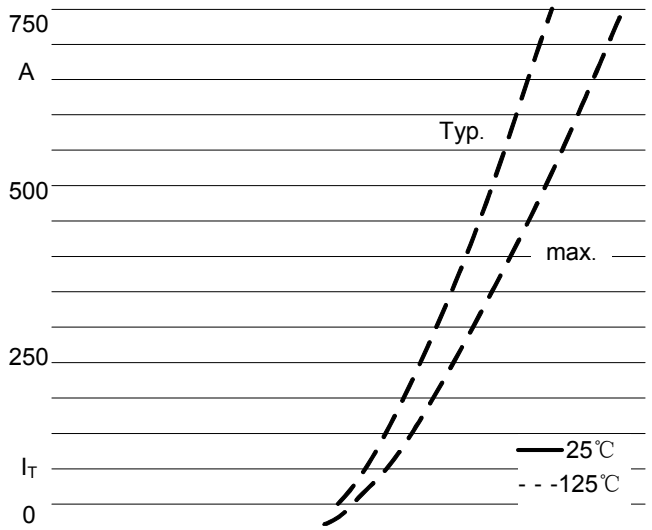


Fig4. Max Non-Repetitive Forward Surge Current



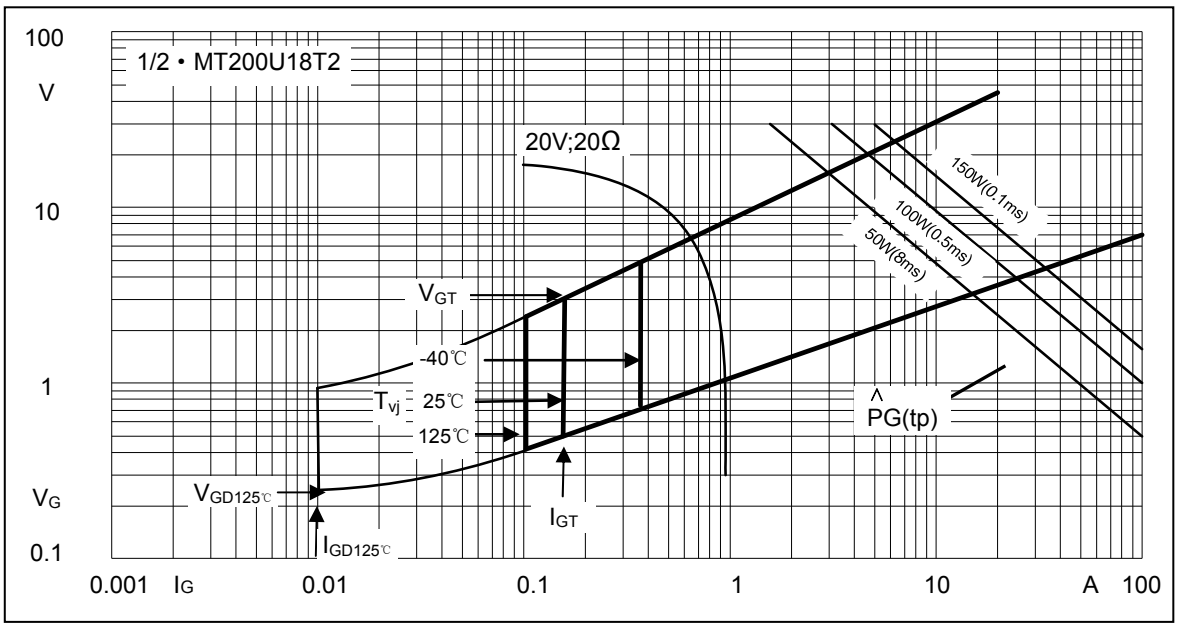


Fig6. Gate trigger Characteristics

Package Outline Information

CASE: T2

